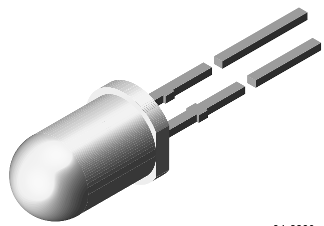
High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero

Description

TSHG6200 is a high speed infrared emitting diode in GaAlAs double hetero (DH) technology, molded in a clear, untinted plastic package.

The new technology combines high speed with high radiant power at wavelength of 850 nm.



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Features

- High modulation bandwidth
- Extra high radiant power and radiant intensity
- Low forward voltage
- Suitable for high pulse current operation
- Standard package T-1¾ (∅ 5 mm)
- Angle of half intensity $\varphi = \pm 10°$
- Peak wavelength $\lambda_p = 850$ nm
- High reliability
- Good spectral matching to Si photodetectors
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

Pb
Pb-free

e2

Applications

- Infrared radiation source for CMOS cameras (illumination). High speed IR data transmission.

Parts Table

Part	Remarks
TSHG6200	MOQ: 4000 pc

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100$ µs	I_{FM}	200	mA
Surge forward current	$t_p = 100$ µs	I_{FSM}	1	A
Power dissipation		P_V	250	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq 5$ sec, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ ambient		R_{thJA}	300	K/W

Basic Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I_F = 100 mA, t_p = 20 ms	V_F		1.5	1.8	V
	I_F = 1 A, t_p = 100 µs	V_F		2.3		V
Temp. coefficient of V_F	I_F = 100 mA	TK_{VF}		- 2.1		mV/K
Reverse current	V_R = 5 V	I_R			10	µA
Junction capacitance	V_R = 0 V, f = 1 MHz, E = 0	C_j		125		pF
Radiant intensity	I_F = 100 mA, t_p = 20 ms	I_e	80	160	400	mW/sr
	I_F = 1 A, t_p = 100 µs	I_e		1600		mW/sr
Radiant power	I_F = 100 mA, t_p = 20 ms	ϕ_e		50		mW
Temp. coefficient of ϕ_e	I_F = 100 mA	$TK\phi_e$		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I_F = 100 mA	λ_p		850		nm
Spectral bandwidth	I_F = 100 mA	$\Delta\lambda$		40		nm
Temp. coefficient of λ_p	I_F = 100 mA	$TK\lambda_p$		0.25		nm/K
Rise time	I_F = 100 mA	t_r		20		ns
Fall time	I_F = 100 mA	t_f		13		ns
Cut-off frequency	I_{DC} = 70 mA, I_{AC} = 30 mA pp	f_c		20		MHz
Virtual source diameter		∅		3.7		mm

Typical Characteristics

T_{amb} = 25 °C, unless otherwise specified

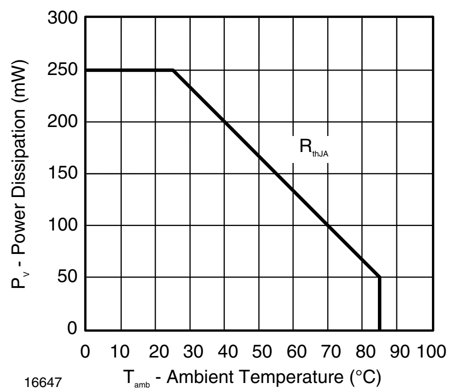


Figure 1. Power Dissipation vs. Ambient Temperature

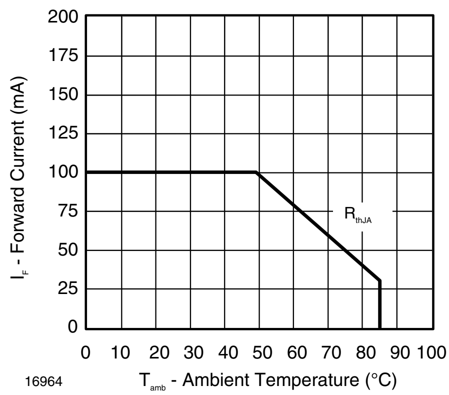


Figure 2. Forward Current vs. Ambient Temperature

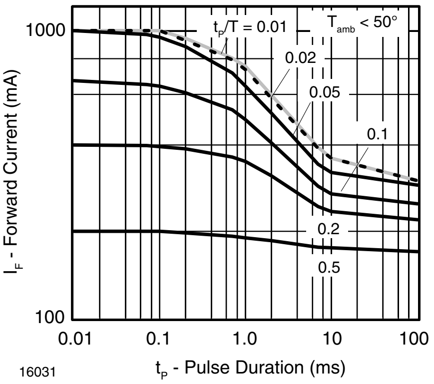


Figure 3. Pulse Forward Current vs. Pulse Duration

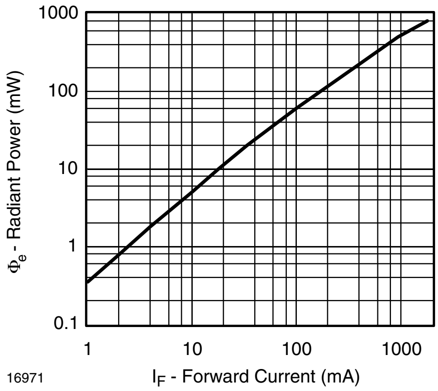


Figure 6. Radiant Power vs. Forward Current

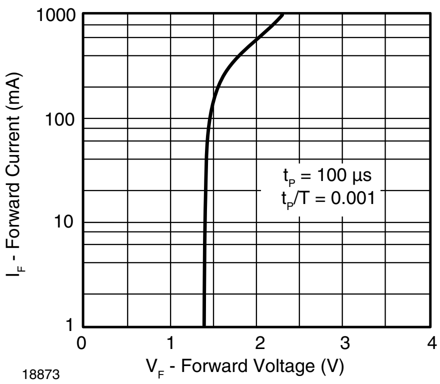


Figure 4. Forward Current vs. Forward Voltage

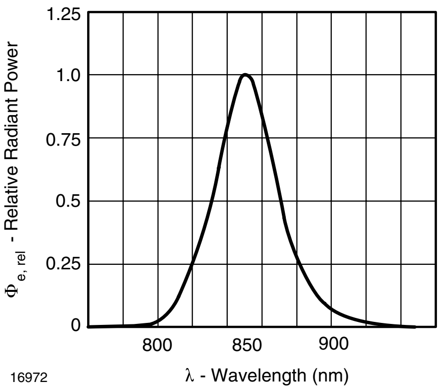


Figure 7. Relative Radiant Power vs. Wavelength

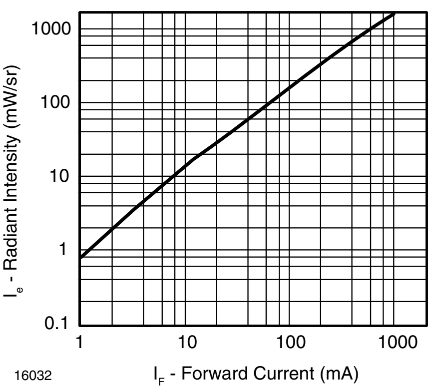


Figure 5. Radiant Intensity vs. Forward Current

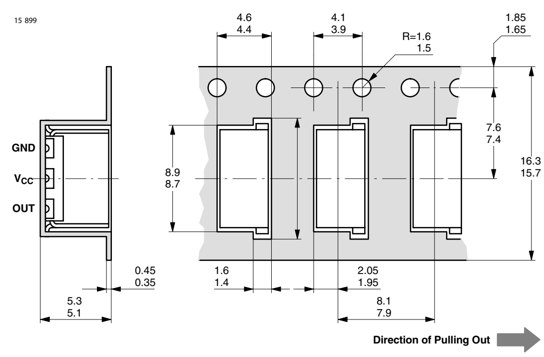
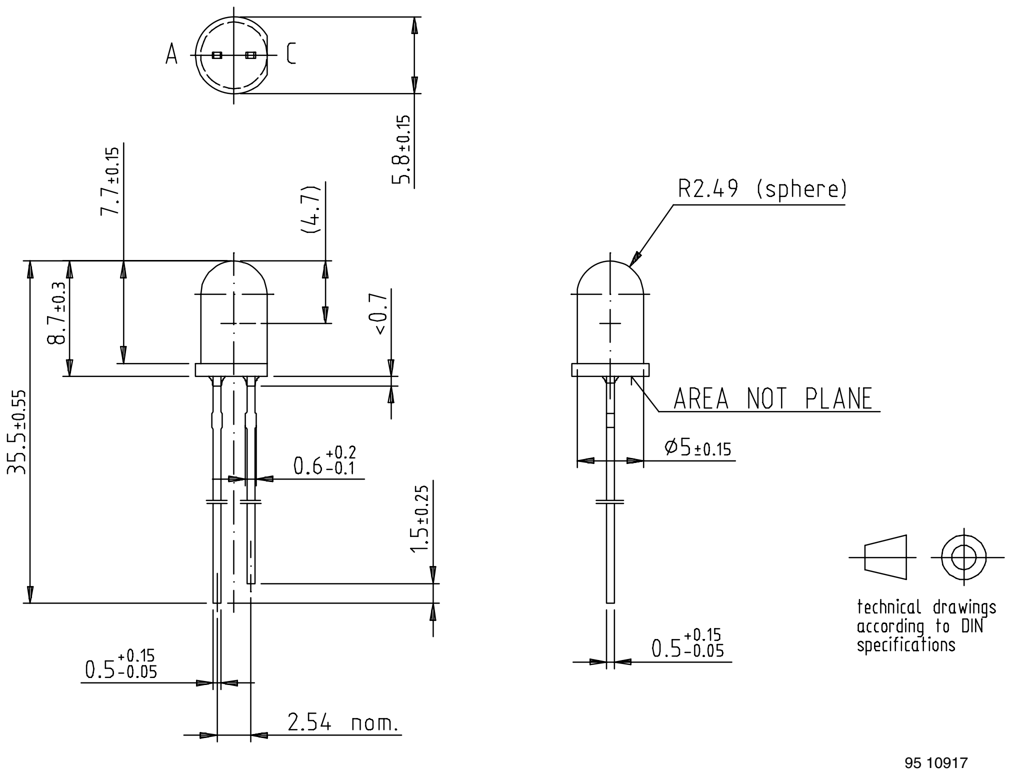


Figure 8. Relative Radiant Intensity vs. Angular Displacement

Package Dimensions in mm



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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